

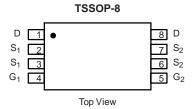
Dual N-Channel 30-V (D-S) MOSFET

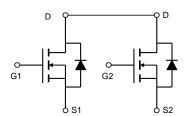
PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)		
30	0.012 at V _{GS} = 10 V	8.6		
	0.019 at V _{GS} = 4.5 V	7.5		

FEATURES

- Halogen-free Option Available
- TrenchFET® Power MOSFETs







ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unles	s otherwise n	oted			
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	30		V	
Gate-Source Voltage		V_{GS}	± 20		V	
0 1 0 1 7 150 00 3	T _A = 25 °C	ı	8.6	7.2		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C	I _D	7.5	5.5	^	
Pulsed Drain Current		I _{DM}	30		А	
Continuous Source Current (Diode Conduction) ^a		I _S	1.5	1.0		
	T _A = 25 °C	D	1.6	1.2	١٨/	
Maximum Power Dissipation ^a	T _A = 70 °C	P_{D}	0.98	0.67	W	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Тур.	Max.	Unit
Mariana haria ta Arkinda	t ≤ 10 s	- R _{thJA}	72	83	°C/W
Maximum Junction-to-Ambient ^a	Steady State		100	120	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	55	70	

Notes:

- a. Surface Mounted on FR4 board, $t \le 10 \text{ s.}$
- * Pb containing terminations are not RoHS compliant, exemptions may apply.



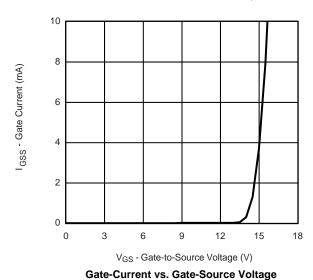
SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions Min.		Typ. ^a	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$ 1.5			3.0	V	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}$			± 200	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$	1		1		
		$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 \text{ °C}$			25	μA	
On-State Drain Current ^b	I _{D(on)}	$V_{DS} \le 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	30			Α	
Drain-Source On-State Resistance ^b	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 8.5 \text{ A}$		0.012			
		$V_{GS} = 4.5 \text{ V}, I_D = 7.5 \text{ A}$		0.019		Ω	
Forward Transconductance ^b	9 _{fs}	$V_{DS} = 15 \text{ V}, I_D = 6.5 \text{ A}$		30		S	
Diode Forward Voltage ^b	V_{SD}	I _S = 1.5 A, V _{GS} = 0 V		0.71	1.2	V	
Dynamic ^a							
Total Gate Charge	Q_g			13			
Gate-Source Charge	Q_{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 6.5 \text{ A}$		2.2		nC	
Gate-Drain Charge	Q_{gd}			3.6			
Turn-On Delay Time	t _{d(on)}			245	365		
Rise Time	t _r	V_{DD} = 15V , R_L = 10 Ω		330	495	20	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ 1 A, V_{GEN} = 4.5 V, R_G = 6 Ω		860	1300	ns	
Fall Time	t _f			510	765		

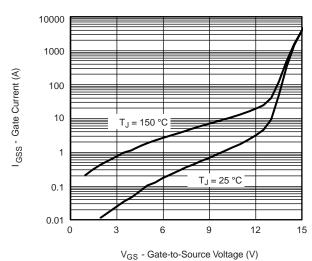
Notes:

- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

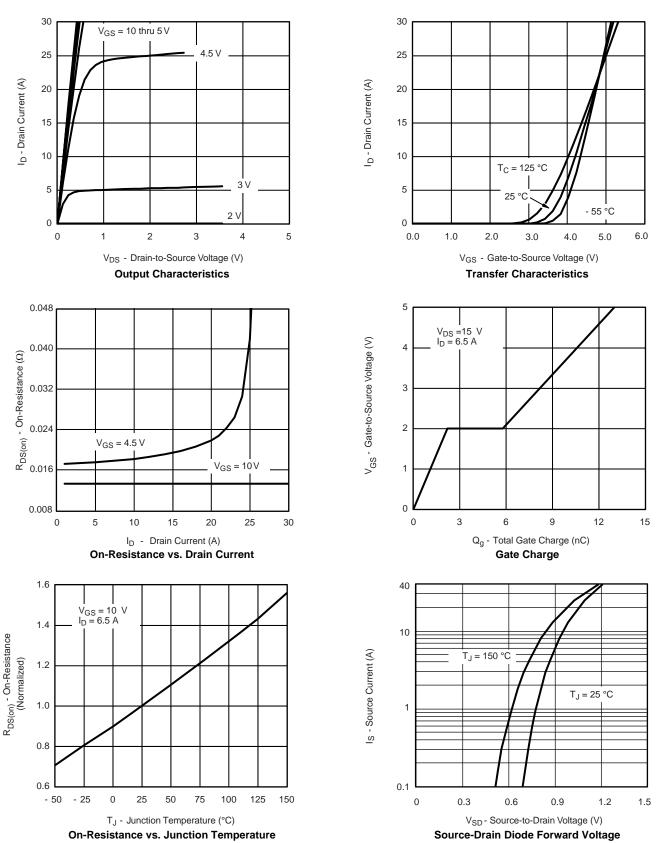




Gate Current vs. Gate-Source Voltage

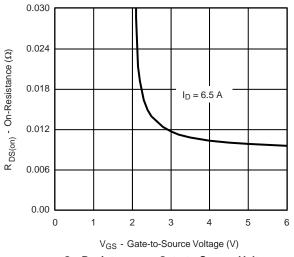


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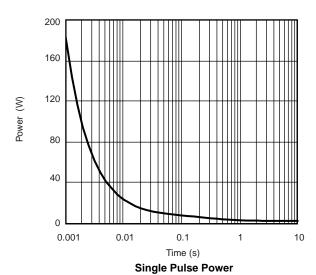


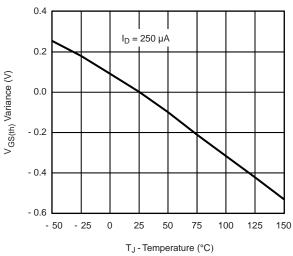


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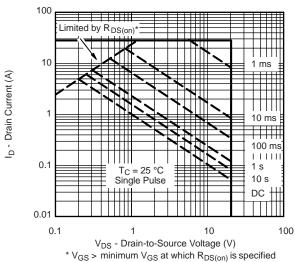


On-Resistance vs. Gate-to-Source Voltage

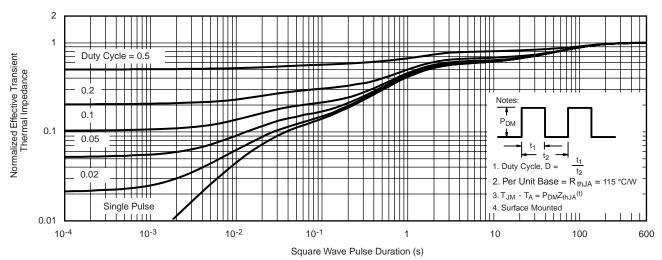




Threshold Voltage



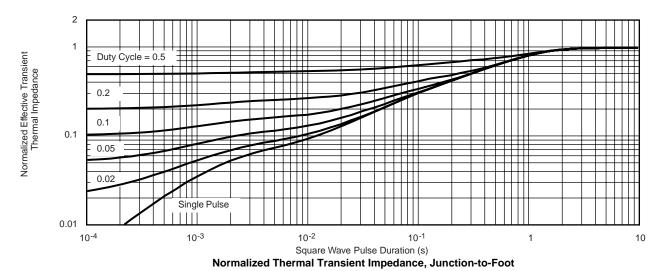
Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient



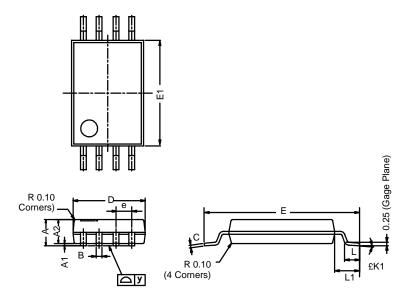
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





TSSOP: 8-LEAD

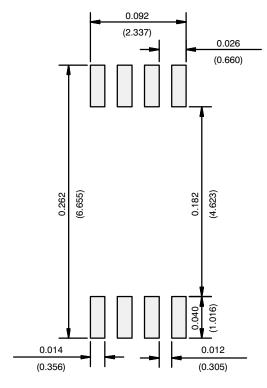
JEDEC Part Number: MO-153



	5.44				
	MILLIMETERS				
Dim	Min	Nom	Max		
Α	-	-	1.20		
A ₁	0.05	0.10	0.15		
A ₂	0.80	1.00	1.05		
В	0.19	0.28	0.30		
С	-	0.127	-		
D	2.90	3.00	3.10		
E	6.20	6.40	6.60		
E ₁	4.30	4.40	4.50		
е	-	0.65	-		
L	0.45	0.60	0.75		
L ₁	0.90	1.00	1.10		
Υ	-	-	0.10		
£ K1	0°	3°	6°		
ECN: S-03946—Rev. G, 09-Jul-01 DWG: 5844					



RECOMMENDED MINIMUM PADS FOR TSSOP-8



Recommended Minimum Pads Dimensions in Inches/(mm)



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